

THE SPECIFICATION OF AlGaAs IR LED CHIP “YL-C883nM-4mW”

1. DESCRIPTION

This is a AlGaAs infrared LED chip. It is N-side up. The peak wavelength is 883 nm (Typ.).

2. ELECTRO - OPTICAL CHARACTERISTICS (Ta=25 deg.C)

CONDITION	Symbol	Condition	MIN.	TYP.	MAX.	UNIT
Forward Voltage	Vf	IF=20mA		1.40		V
Reverse Voltage	Vr	IR=10uA	5			V
Radiated Power ¹⁾	Po	IF=20mA	4.0			mW
Peak Wavelength	λ_p	IF=20mA	878	883	892	nm
Spectral Radiation Bandwidth	$\Delta\lambda$	IF=20mA		55		nm
Rise Time	Tr	IFp=100mA Tw=125ns,Duty=25%		20		ns
Fall Time	Tf	IFp=100mA Tw=125ns,Duty=25%		20		ns
PeakForward Voltage	Vfm	IFp=200mA Tw=10us,Duty=10%		1.90		V

1) LED chip is mounted on TO-18 gold header without resin coated.

3. ABSOLUTE MAXIMUM RATINGS

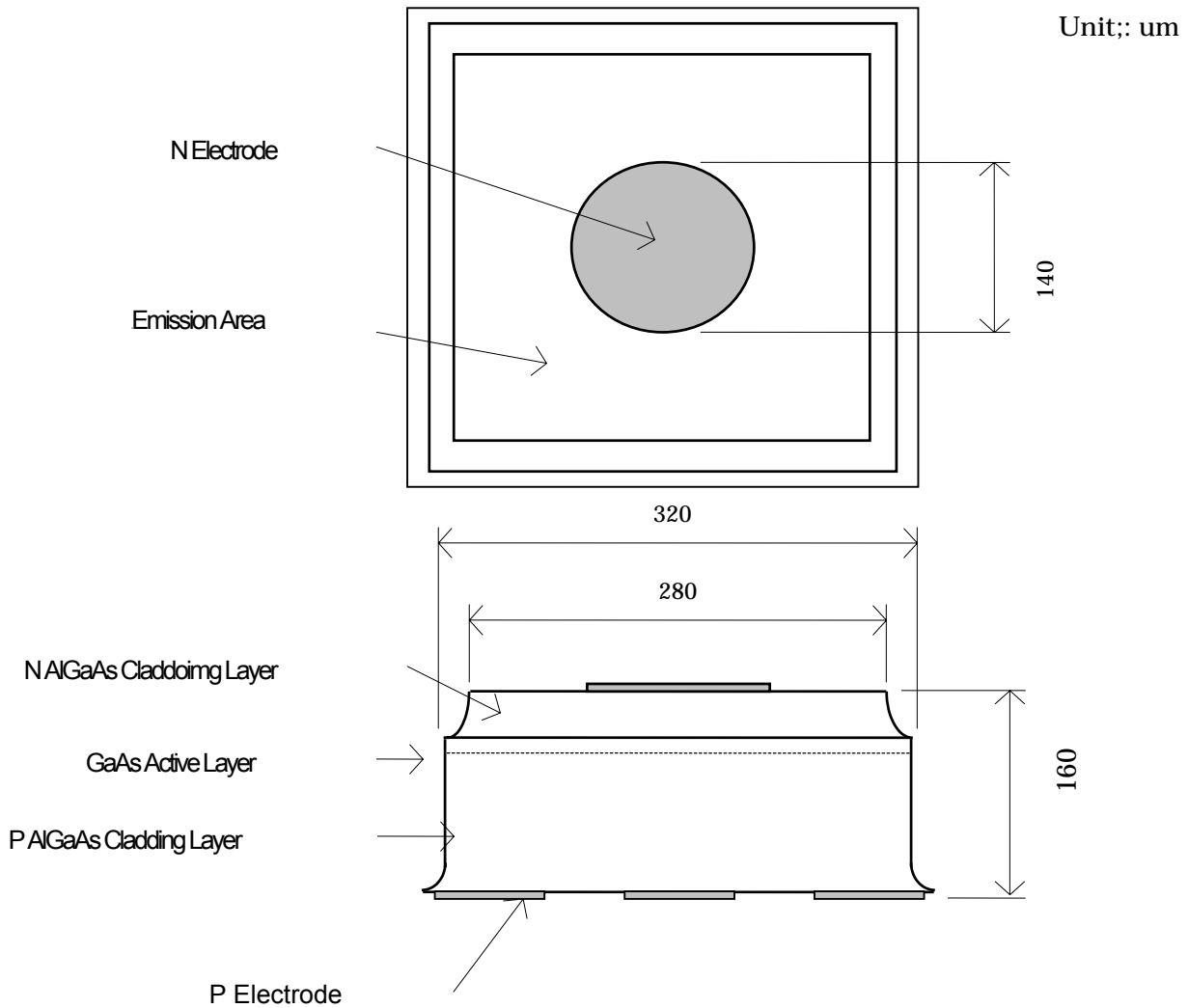
Continuous Maximum Forward Current	: 100 mA(DC)
Continuous Maximum Pulse Current	: 400 mA (Tw=100us,Duty=10%,Tj<120 deg.C)
Reverse Voltage	: 5 V(IR=10uA)
Storage Temperature	
while on mylar membrane	: 0 to 40 deg. C
after removal from mylar membrane	: -40 to 100 deg. C

4. PHYSICAL CHARACTERISTICS AND STRUCTURE

1)Material	: AlGaAs
2)Structure	: Double Hetero Structure
3)Junction Size	: 0.320mmX0.320mm
4)Thickness	: 0.160mm
5)Bond Pad Size	: 0.140mm diameter
6)Anode Metallization	: Gold Alloy
7)Cathode Metallization	: Gold Alloy

Physical Dimensions

Model YL-C883nM-4mW



Remark: This specification is for reference purpose only, and subject to change without prior notice.
Approved specification shall be obtained for the regular purchase.